2N4862/2N4863/2N4864

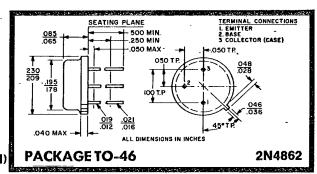


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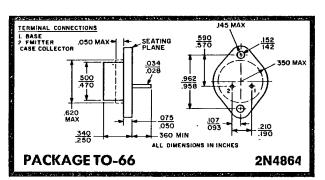
type 2n4862, 2n4863, 2n4864, 2 amp npn SILICON PLANAR

**POWER TRANSISTORS** 

LINEAR he FROM 50 mA TO 2 AMPS HIGH FREQUENCY f<sub>1</sub> = 50 MHz (MINIMUM) LOW SATURATION VOLTAGE AT MAXIMUM **COLLECTOR CURRENT** HIGH VOLTAGE, BV<sub>CEO(sus)</sub> === 120 VOLTS (MINIMUM)



**PACKAGE TO-5** 2N4863



## ABSOLUTE MAXIMUM RATING 25°C AMBIENT (unless otherwise noted)

RATING		SYMBOL	VALUE	COUNT CO
Collector-Base Voltage		V <sub>сво</sub>	140	Volts
Emitter-Base Voltage		V <sub>EBO</sub>	8	Volts
Collector—Emitter Voltage		V <sub>CEO</sub>	120	Volts
Collector Current		l <sub>c</sub>	2	Amps
Base Current		le le	0.5	Amps
Storage Temperature		TstG	-65 to 200	°C
Operating Junction Temperature		T <sub>3</sub> ·	-65 to 200	°C
Dissipation at 100°C Case	: 2N4862	Po	4	Watts
!	2N4863	Po	4	Watts
	2N4864	Pp	16	Watts
Linear Derating Factor*:	2N4862		40	mW/°C
	2N4863		40	mW/°C
	2N4864	· · · · · · · · · · · · · · · · · · ·	160	mW/°C

See Figure No. 1.

## PIRGO ELECTRONICS INC.

A SPRAGUE ELECTRIC COMPANY AFFILIATE **130 CENTRAL AVENUE** 

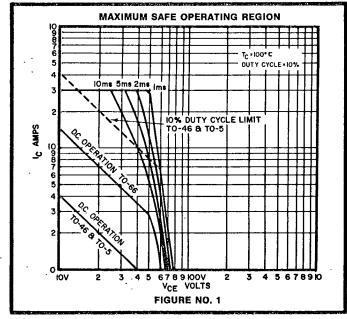
## **2 AMP NPN SILICON PLANAR**

**POWER TRANSISTORS** 

## ELECTRICAL CHARACTERISTICS (25°C Case temperature unless otherwise noted)

<b>有的人</b>	CONDITIONS	LIMIT		
SYMBOL	CONDITIONS	MIN.	MAX.	UNIT;
I <sub>CEX</sub>	$V_{CE} = 60 \text{ V}, V_{BE} = -0.5 \text{ V}, T_{C} = 150^{\circ}\text{C}$		10	μΑ
I <sub>CEX</sub>	$V_{CE} = 140 \text{ V}, V_{BE} = -0.5 \text{ V}$		10	μΑ
Icto	$V_{C8} = 60 \text{ V, I}_{E} = 0$		0.1	μΑ
I <sub>EBO</sub>	V <sub>E8</sub> = 8 V		10	μΑ
BV <sub>CEO(sus)</sub> *	$I_B = 0$ , $I_C = 10 \text{ mA}$	120		Volts
I <sub>CEO</sub>	$I_8 = 0, V_{CE} = 60 \text{ V}$		10	μΑ
h <sub>FE</sub> * .	$I_C = 2 A, V_{CE} = 5 V$	15		
	$I_{c} = 0.5 \text{ A, V}_{ce} = 5 \text{V}$	50	150	
V <sub>CE (sat)</sub> *	$I_{c} = 2 \text{ A}, I_{B} = 0.2 \text{ A}$		1.5	Voits
	$I_{\rm C} = 0.5  \rm A,  I_{\rm B} = 50  mA$		0.2	Volts
V <sub>BE</sub> *	$I_{\rm C}\!=\!0.5{\rm A,V_{CE}}\!=\!5{\rm V}$		1.2	Volts
h <sub>fe</sub>	V <sub>CE</sub> = 10 V, I <sub>C</sub> = 0.1 A, f = 10 MHz	5		
ĥ₁₀	V <sub>CE</sub> = 5 V, I <sub>C</sub> = 50 mA, f = 1 KHz	50		
С。ь	$V_{CB} = 10 \text{ V, } I_C = 0, f = 1 \text{ MHz}$		50	pf

Pulsed measurement: PW ≤ 330 μsec; ≤ 2% duty cycle.



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FOR ADDITIONAL INFORMATION, CONTACT YOUR LOCAL SPRAGUE SALES ENGINEER.

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